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Team Nexperia

# 1. General description

PNP high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

NPN complement: PHPT60410NY

## 2. Features and benefits

- High thermal power dissipation capability
- Suitable for high temperature applications up to 175 °C
- Reduced Printed-Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

# 3. Applications

- Power management
- Load switch
- Linear mode voltage regulator
- Backlighting applications
- Motor drive
- Relay replacement

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-40	V
I <sub>C</sub>	collector current		-	-	-10	Α
I <sub>CM</sub>	peak collector current	$t_p \le 1$ ms; single pulse	-	-	-20	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C}$ = -10 A; $I_{B}$ = -1 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	37	55	mΩ





40 V, 10 A PNP high power bipolar transistor

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter	mb	C
2	Е	emitter		В—
3	Е	emitter	q	'*_
4	В	base	فققف	sym132
mb	С	collector	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

# 6. Ordering information

Table 3. Ordering information

Type number	Package	Package				
	Name	Description	Version			
PHPT60410PY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669			

# 7. Marking

Table 4. Marking codes

Type number	Marking code
PHPT60410PY	0410PAB

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# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	-40	V
$V_{CEO}$	collector-emitter voltage	open base		-	-40	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-8	V
I <sub>C</sub>	collector current			-	-10	Α
I <sub>CM</sub>	peak collector current	t <sub>p</sub> ≤ 1 ms; single pulse		-	-20	Α
I <sub>B</sub>	base current			-	-1	Α
I <sub>BM</sub>	peak base current	t <sub>p</sub> ≤ 1 ms; pulsed		-	-2	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	1.3	W
			[2]	-	3.3	W
			[3]	-	5	W
			[4]	-	25	W
Tj	junction temperature			-	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C

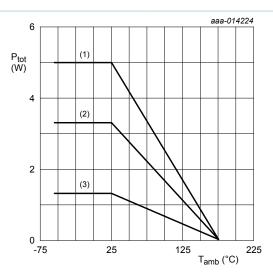
<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Device mounted on an FR4 Printed-Circuit Board ( PCB), single-sided copper, tin-plated mounting pad for collector 6 cm<sup>2</sup>.

<sup>[3]</sup> Device mounted on an ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.

<sup>[4]</sup> Power dissipation from junction to mounting base.

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- (1) Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient		in free air	[1]	-	-	115	K/W
		[2]	-	-	45	K/W	
	ambient		[3]	-	-	30	K/W
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base			-	-	6	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on an ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.

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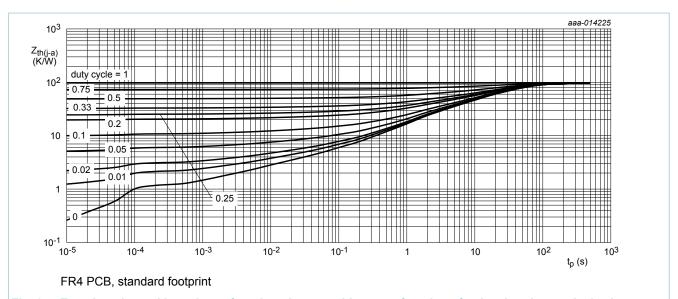


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

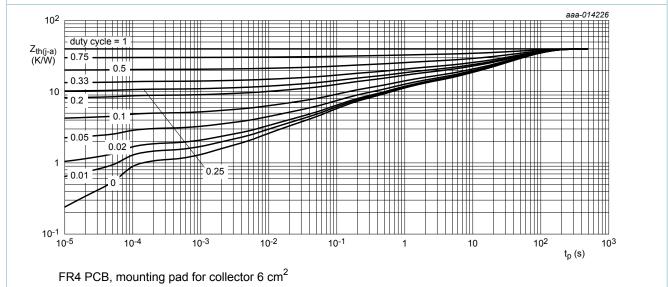


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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# 10. Characteristics

Table 7. Characteristics

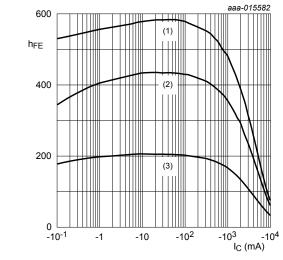
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	$V_{CB}$ = -32 V; $I_E$ = 0 A; $T_{amb}$ = 25 °C	-	-	-100	nA
	current	$V_{CB}$ = -32 V; $I_{E}$ = 0 A; $T_{j}$ = 150 °C	-	-	-50	μA
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE} = -32 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -8 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -2 V; $I_{C}$ = -500 mA; $T_{amb}$ = 25 °C	240	350	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -1 A; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C; pulsed	220	320	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -5 A; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C; pulsed	100	150	-	
		$V_{CE} = -2 \text{ V; } I_{C} = -10 \text{ A; pulsed;}$ $t_{p} \le 300 \text{ µs; } \delta \le 0.02; T_{amb} = 25 ^{\circ}\text{C}$	40	50	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = -1 A; $I_B$ = -50 mA; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	-50	-70	mV
		$I_{C}$ = -5 A; $I_{B}$ = -500 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb} = 25 \ ^{\circ}C$	-	-180	-250	mV
		$I_C$ = -10 A; $I_B$ = -500 mA; pulsed; $t_p \le 300 \text{ μs}$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	-550	-800	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -10 A; $I_B$ = -1 A; pulsed; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	37	55	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C$ = -1 A; $I_B$ = -50 mA; pulsed; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	-	-0.95	V
		$I_C$ = -5 A; $I_B$ = -500 mA; pulsed; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	-	-1.15	V
		$I_C$ = -10 A; $I_B$ = -500 mA; pulsed; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	-	-1.25	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE}$ = -2 V; $I_{C}$ = -500 mA; $T_{amb}$ = 25 °C	-	-	-0.8	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = -12.5 V; I <sub>C</sub> = -5 A;	-	15	-	ns
t <sub>r</sub>	rise time	$I_{Bon} = -250 \text{ mA}; I_{Boff} = 250 \text{ mA};$	-	105	-	ns
t <sub>on</sub>	turn-on time	T <sub>amb</sub> = 25 °C	-	120	-	ns
t <sub>s</sub>	storage time		-	155	-	ns
t <sub>f</sub>	fall time		-	80	-	ns
t <sub>off</sub>	turn-off time		-	235	-	ns

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>T</sub>	transition frequency	$V_{CE}$ = -10 V; $I_{C}$ = -500 mA; f = 100 MHz; $T_{amb}$ = 25 °C	-	97	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB}$ = -10 V; $I_E$ = 0 A; $i_e$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C	-	84	-	pF



 $V_{CE}$  = -2 V

(1)  $T_{amb} = 100 \, ^{\circ}C$ 

(2)  $T_{amb}$  = 25 °C

 $(3) T_{amb} = -55 °C$ 

Fig. 4. DC current gain as a function of collector current; typical values

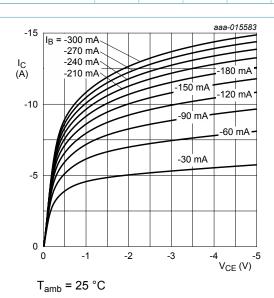
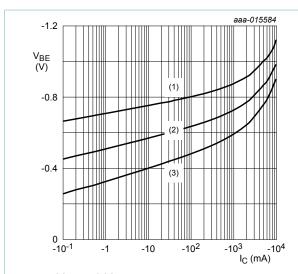


Fig. 5. Collector current as a function of collectoremitter voltage; typical values

40 V, 10 A PNP high power bipolar transistor



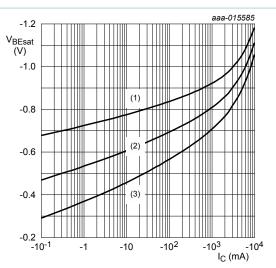
$$V_{CE} = -2 V$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb}$$
 = 100 °C

Fig. 6. Base-emitter voltage as a function of collector current; typical values



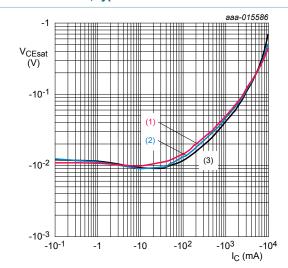
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb}$$
 = 100 °C

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values



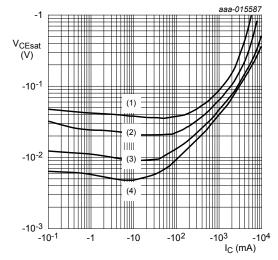
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



(1) 
$$I_C/I_B = 100$$

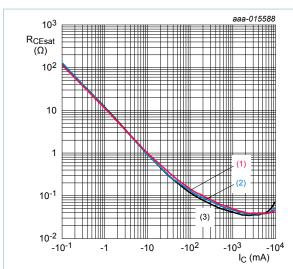
(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 20$$

$$(4) I_C/I_B = 10$$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

## 40 V, 10 A PNP high power bipolar transistor



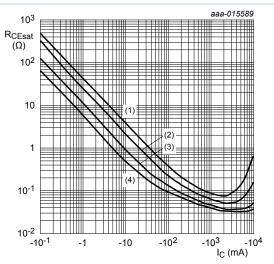
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values



$$T_{amb}$$
 = 25 °C

(1) 
$$I_C/I_B = 100$$

(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 20$$

(4) 
$$I_{\rm C}/I_{\rm B} = 10$$

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

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## 11. Test information

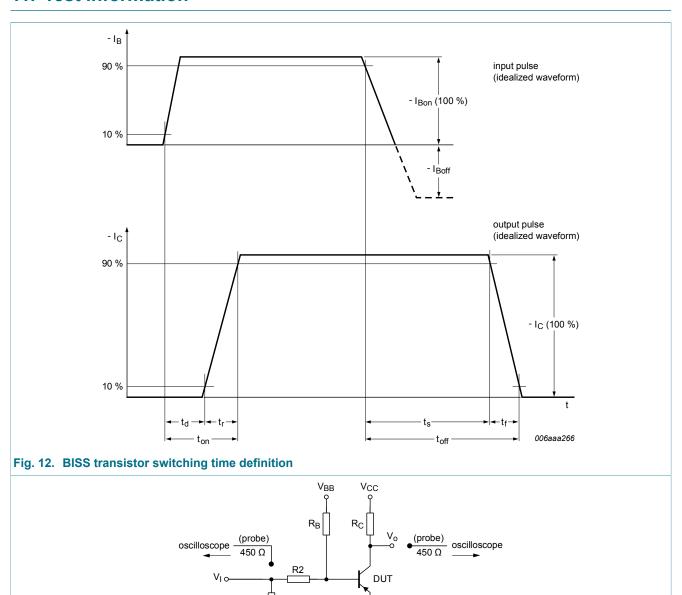


Fig. 13. Test circuit for switching times

## 11.1 Quality information

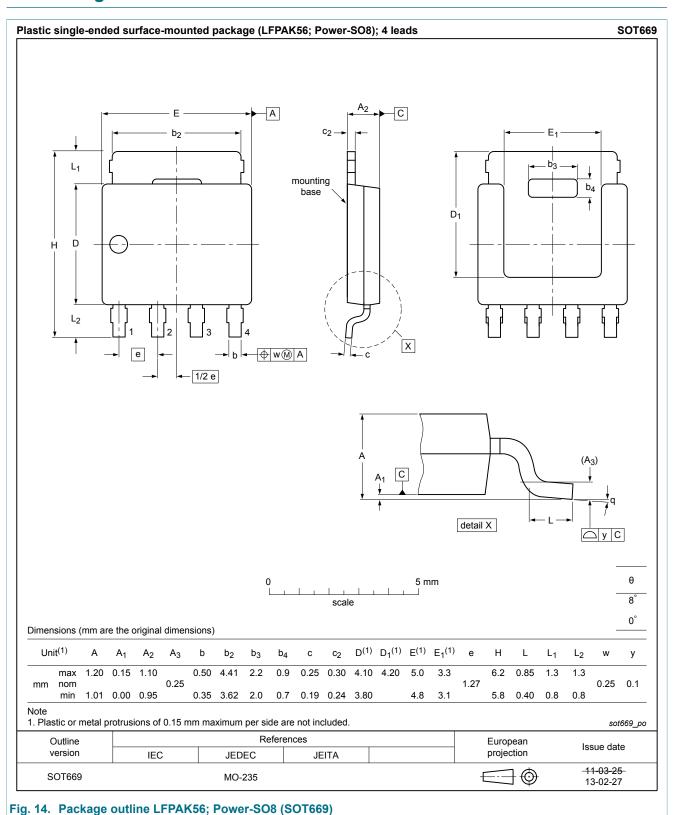
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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# 12. Package outline

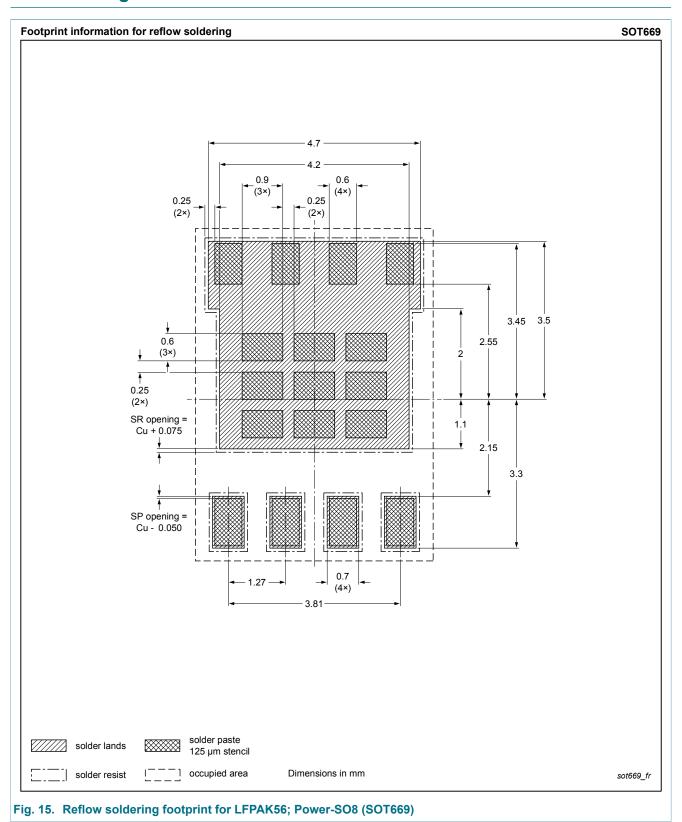


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# 13. Soldering



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# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PHPT60410PY v.1	20150121	Product data sheet	-	-

#### 40 V, 10 A PNP high power bipolar transistor

## 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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